

DATA SHEET

For a complete data sheet, please also download:

- The IC04 LOCMOS HE4000B Logic Family Specifications HEF, HEC
- The IC04 LOCMOS HE4000B Logic Package Outlines/Information HEF, HEC

HEF4060B

MSI

14-stage ripple-carry binary counter/divider and oscillator

Product specification
File under Integrated Circuits, IC04

January 1995

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HEF4060B MSI

DESCRIPTION

The HEF4060B is a 14-stage ripple-carry binary counter/divider and oscillator with three oscillator terminals (RS, R_{TC} and C_{TC}), ten buffered outputs (O₃ to O₉ and O₁₁ to O₁₃) and an overriding asynchronous master reset input (MR). The oscillator configuration allows design of either RC or crystal oscillator circuits. The oscillator may

be replaced by an external clock signal at input RS. The counter advances on the negative-going transition of RS. A HIGH level on MR resets the counter (O₃ to O₉ and O₁₁ to O₁₃ = LOW), independent of other input conditions.

Schmitt-trigger action in the clock input makes the circuit highly tolerant to slower clock rise and fall times.

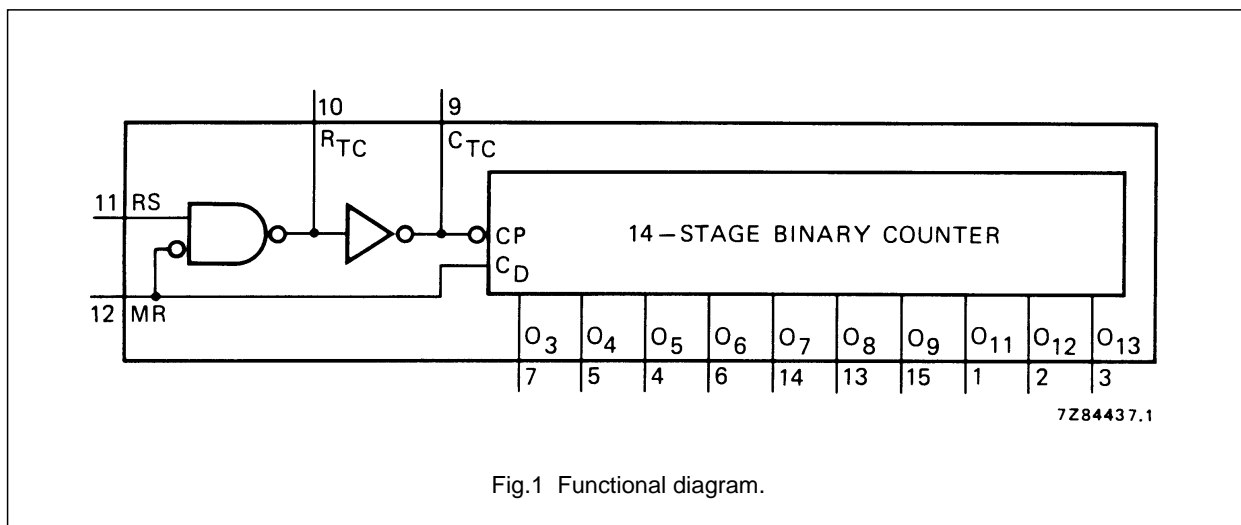


Fig.1 Functional diagram.

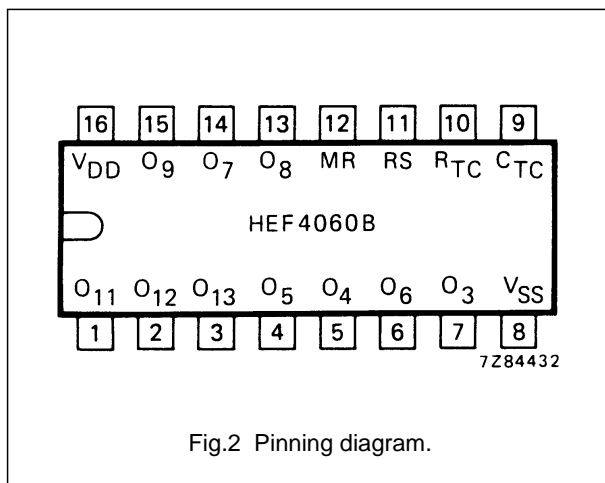


Fig.2 Pinning diagram.

PINNING

- MR master reset
- RS clock input/oscillator pin
- R_{TC} oscillator pin
- C_{TC} external capacitor connection
- O₃ to O₉ counter outputs
- O₁₁ to O₁₃ counter outputs

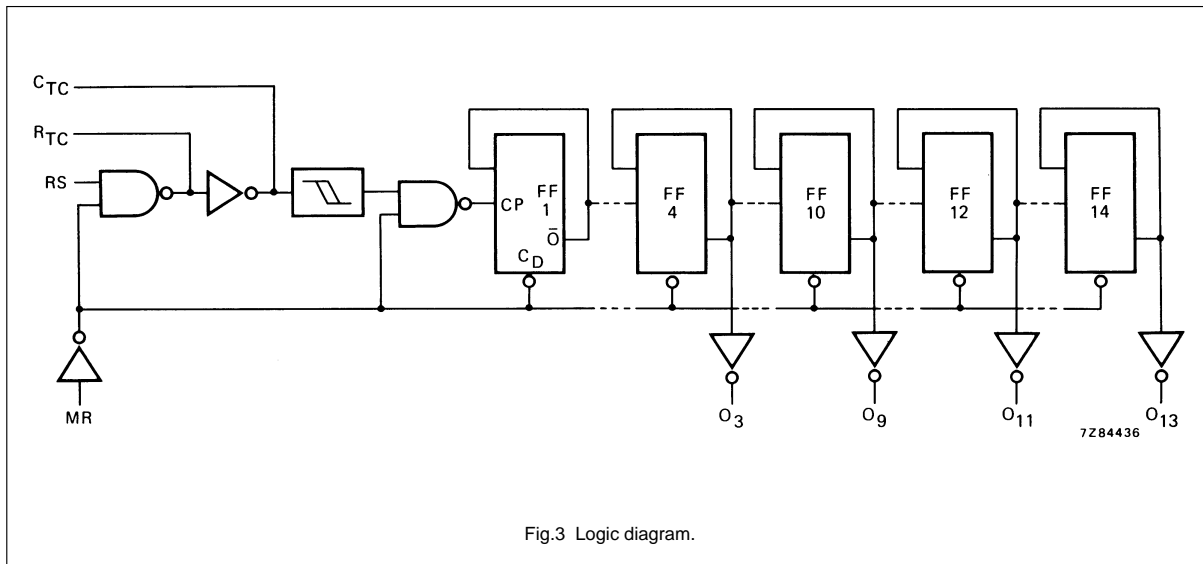
- HEF4060BP(N): 16-lead DIL; plastic (SOT38-1)
- HEF4060BD(F): 16-lead DIL; ceramic (cerdip) (SOT74)
- HEF4060BT(D): 16-lead SO; plastic (SOT109-1)
- (): Package Designator North America

FAMILY DATA, I_{DD} LIMITS category MSI

See Family Specifications

14-stage ripple-carry binary counter/divider
and oscillator

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AC CHARACTERISTICS

$V_{SS} = 0$ V; $T_{amb} = 25$ °C; $C_L = 50$ pF; input transition times ≤ 20 ns

	V_{DD} V	SYMBOL	MIN.	TYP.	MAX.	TYPICAL EXTRAPOLATION FORMULA							
Propagation delays	5	t_{PHL}		210	420	ns	183 ns + (0,55 ns/pF) C_L						
								HIGH to LOW	10	80	160	ns	69 ns + (0,23 ns/pF) C_L
	5	t_{PLH}		210	420	ns	183 ns + (0,55 ns/pF) C_L						
								LOW to HIGH	10	80	160	ns	69 ns + (0,23 ns/pF) C_L
	5	t_{PHL}		25	50	ns							
								HIGH to LOW	10	10	20	ns	
	5	t_{PLH}		25	50	ns							
								LOW to HIGH	10	10	20	ns	
5	t_{PHL}		100	200	ns	73 ns + (0,55 ns/pF) C_L							
							MR \rightarrow O_n HIGH to LOW	10	40	80	ns	29 ns + (0,23 ns/pF) C_L	
													15
5	t_{THL}		60	120	ns	10 ns + (1,0 ns/pF) C_L							
							Output transition times HIGH to LOW	10	30	60	ns	9 ns + (0,42 ns/pF) C_L	
													15
5	t_{TLH}		60	120	ns	10 ns + (1,0 ns/pF) C_L							
							LOW to HIGH	10	30	60	ns	9 ns + (0,42 ns/pF) C_L	
													15
5	t_{WRSH}		120	60	ns								
							Minimum clock pulse width input RS HIGH	10	50	25	ns		
													15
5	t_{WMRH}		50	25	ns								
							Minimum MR pulse width; HIGH	10	30	15	ns		
													15
5	t_{RMR}		160	80	ns								
							Recovery time for MR	10	80	40	ns		
													15
5	f_{max}		4	8	MHz								
							Maximum clock pulse frequency input RS	10	10	20	MHz		
													15

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$V_{SS} = 0$ V; $T_{amb} = 25$ °C; input transition times ≤ 20 ns

	V_{DD} V	TYPICAL FORMULA FOR P (μ W) ⁽¹⁾
Dynamic power dissipation per package (P)	5	$700 f_i + f_o C_L V_{DD}^2$
	10	$3\,300 f_i + f_o C_L V_{DD}^2$
	15	$8\,900 f_i + f_o C_L V_{DD}^2$
Total power dissipation when using the on-chip oscillator (P)	5	$700 f_{osc} + f_o C_L V_{DD}^2 + 2C_t V_{DD}^2 f_{osc} + 690 V_{DD}$
	10	$3\,300 f_{osc} + f_o C_L V_{DD}^2 + 2C_t V_{DD}^2 f_{osc} + 6\,900 V_{DD}$
	15	$8\,900 f_{osc} + f_o C_L V_{DD}^2 + 2C_t V_{DD}^2 f_{osc} + 22\,000 V_{DD}$

Notes

1. where:

f_i = input frequency (MHz)

f_o = output frequency (MHz)

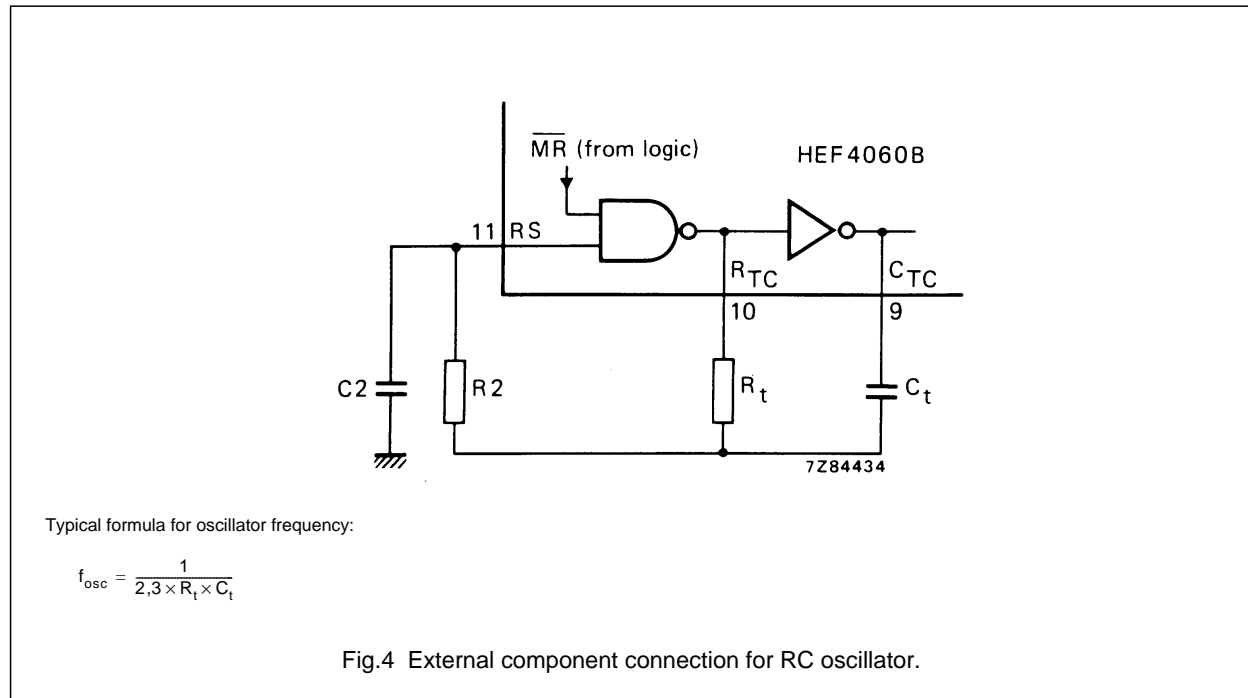
C_L = load capacitance (pF)

V_{DD} = supply voltage (V)

C_t = timing capacitance (pF)

f_{osc} = oscillator frequency (MHz)

RC oscillator



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Timing component limitations

The oscillator frequency is mainly determined by $R_t C_t$, provided $R_t \ll R_2$ and $R_2 C_2 \ll R_t C_t$. The function of R_2 is to minimize the influence of the forward voltage across the input protection diodes on the frequency. The stray capacitance C_2 should be kept as small as possible. In consideration of accuracy, C_t must be larger than the inherent stray capacitance. R_t must be larger than the LOCMOS 'ON' resistance in series with it, which typically is 500Ω at $V_{DD} = 5 \text{ V}$, 300Ω at $V_{DD} = 10 \text{ V}$ and 200Ω at $V_{DD} = 15 \text{ V}$.

The recommended values for these components to maintain agreement with the typical oscillation formula are:

$C_t \geq 100 \text{ pF}$, up to any practical value,
 $10 \text{ k}\Omega \leq R_t \leq 1 \text{ M}\Omega$.

Typical crystal oscillator circuit

In Fig.5, R_2 is the power limiting resistor. For starting and maintaining oscillation a minimum transconductance is necessary.

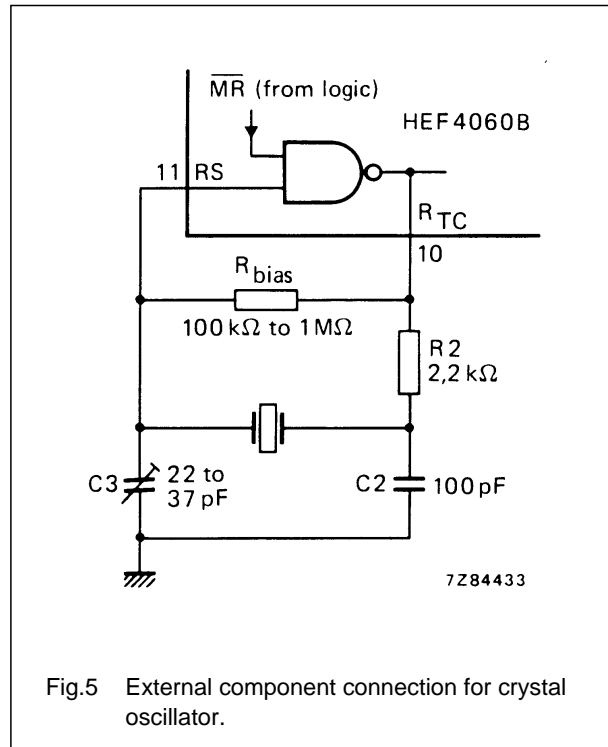


Fig.5 External component connection for crystal oscillator.

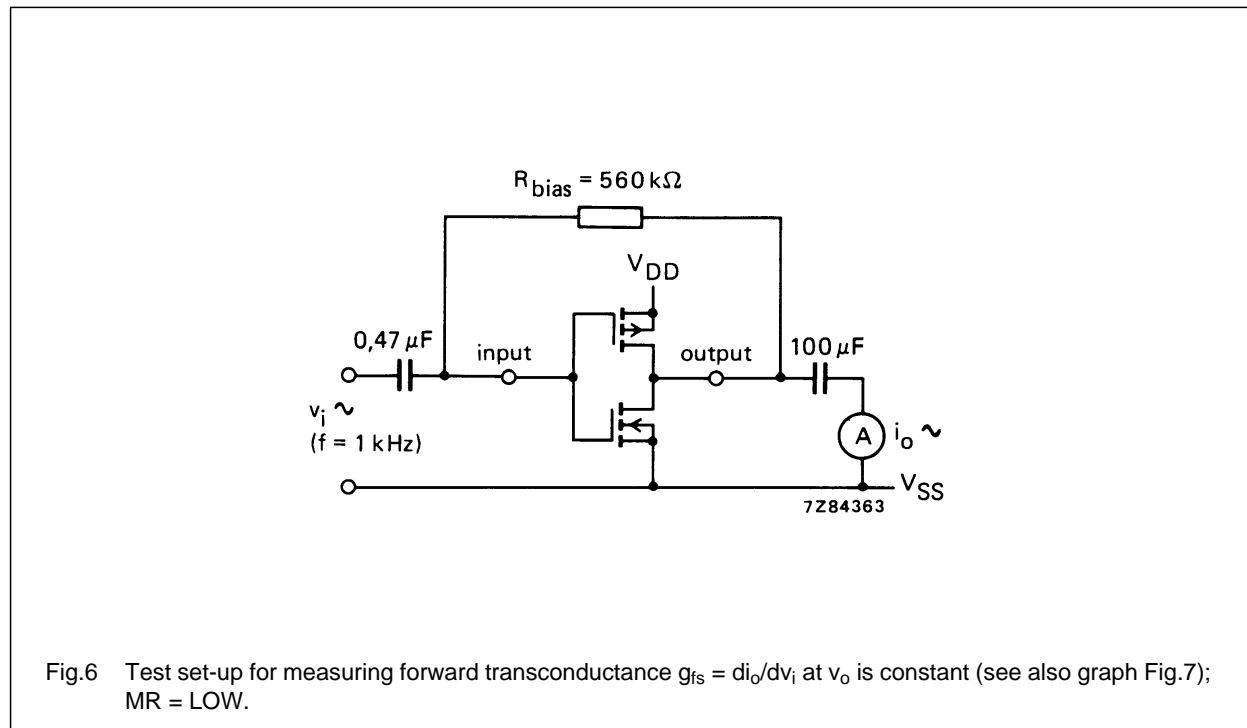


Fig.6 Test set-up for measuring forward transconductance $g_{fs} = di_o/dv_i$ at v_o is constant (see also graph Fig.7); $MR = \text{LOW}$.

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